



AP22913

SINGLE SLEW RATE CONTROLLED LOAD SWITCH

Description

The AP22913 slew rate controlled load switch is a single P-channel MOSFET power switch designed for high-side load-switching applications. The MOSFET has a typical $R_{DS(on)}$ of $54m\Omega$ at 5V (X1-WLB0909-4), allowing increased load current handling capacity with a low forward voltage drop. The turn-on slew rate of the device is controlled internally. V_{IN} and V_{OUT} are isolated during the OFF state with a TRCB (True Reverse Current Blocking) feature.

The AP22913 load switch is designed to operate from 1.4V to 5.5V, making it ideal for 1.8V, 2.5V, 3.3V, and 5V systems. The typical quiescent supply current is only $1\mu A$.

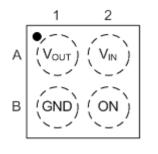
The AP22913 is available in the wafer level chip scale 4-pin, X1-WLB0909-4 0.5mm pitch and standard SOT26 package.

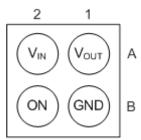
Features

- Wide Input Voltage Range: 1.4V to 5.5V
- Low On-Resistance (X1-WLB0909-4):
 - 92mΩ Typical @1.5V
 - 76mΩ Typical @1.8V
 - 56mΩ Typical @3.3V
 - 54mΩ Typical @5.0V
- High DC Current Capability up to 2A
- Truly Reverse Current Block (TRCB)
- Discharging Resistor on V_{OUT} When Disabled
- Ultra-Low Quiescent Current 1µA
- Active-High Control Pin
 - Minimum 1.1V V_{IH} of ON
- ESD Protection:
 - Human Body Model: 2kV
 - Charged Device Model: 1kV
- Package:
 - SX1-WLB0909-4 with Backside Laminate
 - Standard Green SOT26
 - 0.9mm x 0.9mm, 0.5mm Ball Pitch
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- For automotive applications requiring specific change control (i.e. parts qualified to AEC-Q100/101/200, PPAP capable, and manufactured in IATF 16949 certified facilities), please contact us or your local Diodes representative. https://www.diodes.com/quality/product-definitions/

Pin Assignments

X1-WLB0909-4

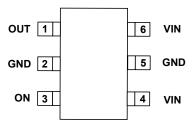




Top View

Bottom View

SOT26



Top View

Applications

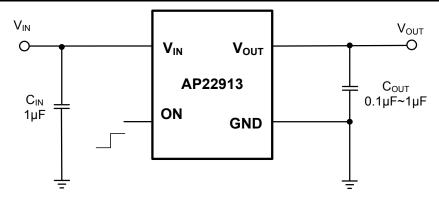
- Mobile Device and Smart Phones
- Portable Media Devices
- Wearable Devices
- Advanced Notebooks, UMPC and MID
- Portable Medical Devices
- GPS and Navigation Equipment

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
- 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.



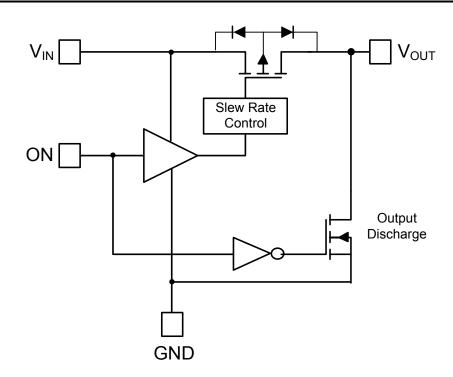
Typical Applications Circuit



Pin Descriptions

Pin Name	Pin Number	Function
Pin Name	WLCSP	Function
V _{OUT}	A1	Voltage output pin. This is the pin to the P-channel MOSFET drain connection. Bypass to ground through a 0.1μF or 1μF capacitor.
V _{IN}	A2	Voltage input pin. This is the pin to the P-channel MOSFET source. Bypass to ground through a 1µF capacitor.
GND	B1	Ground.
ON	B2	Enable input, active high

Functional Block Diagram





Absolute Maximum Ratings (@ T_A = +25°C, unless otherwise specified.)

Symbol	Parameter	Rat	ings	Unit
ESD HBM	Human Body Model ESD Protection		6	kV
ESD CDM	Charged Device Model ESD Protection	:	2	kV
V _{IN}	Input Voltage	-0.3	to 6	V
V _{OUT}	Output Voltage	-0.3	to 6	V
V _{ON}	ON Voltage	-0.3	to 6	V
I _{LOAD}	Maximum Continuous Load Current	:	2	A
I _{LOAD}	Maximum Pulse Load Current, Pulse <300µs, 2% Duty Cycle	2.5		Α
TJ	Maximum Junction Temperature +125		°C	
T _{ST}	Storage Temperature Range -65 to +150		°C	
P _D	Power Dissipation	WLB0909-4	930	mW
ט י	1 Ower Dissipation	SOT-26	760	111111
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient (Note 4)	WLB0909-4	136	°C/W
NejA	memaritesistance, sunction to Ambient (Note 4)	SOT-26	165	- C/VV
R _{eJC}	Thermal Resistance, Junction to Case (Note 5)	WLB0909-4	31	°C/W
000	(1000)	SOT-26	30	

Notes:

Caution

Stresses greater than the 'Absolute Maximum Ratings' specified above may cause permanent damage to the device. These are stress ratings only; functional operation of the device at these or any other conditions exceeding those indicated in this specification is not implied. Device reliability may be affected by exposure to absolute maximum rating conditions for extended periods of time.

Recommended Operating Conditions (@ T_A = +25°C, unless otherwise specified.)

Symbol	P	Parameter		Max	Unit
V _{IN}	Input Voltage		1.4	5.5	V
V _{ON}	ON Voltage Range		0	5.5	V
V _{OUT}	Output Voltage	Output Voltage		5.5	V
I _{OUT}	Output Current	Output Current		2.0	Α
V _{IH}	ON High-Level Input Vo	ON High-Level Input Voltage		5.5	V
	ON Low-Level Input	V _{IN} = 3.6V to 5.5V	0	0.6	V
V _{IL}	Voltage	V _{IN} = 1.4V to 3.6V	0	0.4	V
TA	Operating Ambient Tem	Operating Ambient Temperature		+85	°C

^{4.} The JEDEC high-K (2s2p) board used to derive this data was a 3 inch x 3 inch, multilayer board with 1oz internal power and ground planes with2oz copper traces on top and bottom of the board.

^{5.} Thermal resistance from junction to case.



Electrical Characteristics ($T_A = -40$ °C to +85°C, $V_{IN} = 1.4$ to 5.5V, $V_{ON} = V_{IN}$ (Enabled), $V_{ON} = 0$ V (Disabled), $C_{IN} = 1\mu$ F, $C_{OUT} = 0.1\mu$ F, unless otherwise specified.) (Note 6)

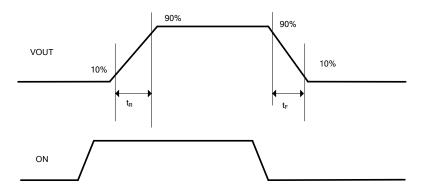
Symbol	Parameters	Test Conditi	ons	Min	Тур	Max	Unit
	Input Quiescent Current		V _{IN} = 5.25V	_	1.4	7	
			V _{IN} = 4.2V	_	1	5	
IQ		$I_{OUT} = 0mA$,	V _{IN} = 3.6V	_	0.7	5	μA
		V _{ON} = Enabled	$V_{IN} = 2.5V$	_	0.5	3.5	
			V _{IN} = 1.5V	_	0.3	3.5	
			V _{IN} = 5.25V	_	0.1	1	
		$R_L = 1M\Omega$,	$V_{IN} = 4.2V$	_	0.1	1	
I _{SHDN}	Input Shutdown Current		V _{IN} = 3.6V	_	0.1	1	μA
2	·	V _{ON} = Disabled	V _{IN} = 2.5V	_	0.1	1	·
			V _{IN} = 1.5V	_	0.1	1	
			V _{IN} = 5.25V	_	0.1	2	
			$V_{IN} = 4.2V$	_	0.1	2	
I _{IN LEAK}	Input Leakage Current	$V_{OUT} = 0V$,	$V_{IN} = 3.6V$	_	0.1	2	μΑ
·IIV_LLAK	, at a contage of an entity	V _{ON} = Disabled	$V_{IN} = 2.5V$	_	0.1	2	μ
			$V_{IN} = 1.5V$	_	0.1	2	
			+25°C		54	70	
		$V_{IN} = 5.0V$	Full	_	_	95	
			+25°C	_	55	70	
		V _{IN} = 4.2V	Full	_	_	95	
		.,	+25°C	_	56	80	
	Switch On-resistance, I _{OUT} = -200mA at X1-WLB0909-4 package	$V_{IN} = 3.3V$	Full	_	_	95	m O
		V _{IN} = 2.5V	+25°C	_	60	85	mΩ
			Full	_	_	115	
		V _{IN} = 1.8V V _{IN} = 1.5V	+25°C	_	76	100	
			Full	_	_	130	
			+25°C	_	92	120	
R _{DS(on)}			Full	_	<u> </u>	150	
= 5(511)		V _{IN} = 5.0V	25°C		84	100	
			Full 25°C		— 85	125 100	
		V _{IN} = 4.2V	Full		- 00	125	
			25°C		86	100	
	Switch On-resistance, I _{OUT} = -200mA at	$V_{IN} = 3.3V$	Full	_	_	125	mΩ
	SOT26 package		25°C	_	90	115	
		$V_{IN} = 2.5V$	Full	_	_	145	
		\/ = 1 9\/	25°C	_	106	130	
		V _{IN} = 1.8V	Full	_	_	160	
		V _{IN} = 1.5V	25°C	_	122	150	
			Full	_	_	180	
R _{DIS}	Discharge FET On-resistance	$V_{IN} = 3.3V$, $V_{ON} = 0V$, $I_{OUT} = 30$ mA, $T_A = +25$ °C		_	150	200	Ω
11/4.0	Lindonyoltaga Laaksiit	V _{IN} increasing		_	_	1.2	\/
UVLO	Undervoltage Lockout	V _{IN} decreasing		0.5	_	_	V
V _{T_RCB}	TRCB Trigger Point	Vout - Vin		_	44	_	mV
V _{R_RCB}	TRCB Release Point	Vin - Vout		_	0	_	mV
t _{T_RCB}	TRCB Response Time	$V_{IN} = 5V, V_{ON} = V_{IN}$		_	10	_	μs
I _{RCB}	TRCB Reverse Leakage Current (Current from V _{IN})	V _{OUT} - V _{IN} > V _{T_RCB} , V _{ON} = Enabled		_	0.3	_	μA
		V _{IN} = 0V, V _{OUT} = 5.5V, V _{ON} = Disabled		ļ		4	^
I _{ON}	ON Input Leakage	V_{ON} = 0V, 5.25V or V_{ON} = V_{IN}		_	_	1	μA

Note: 6. Specifications are over -40°C to +85°C and are guaranteed by characterization and design.

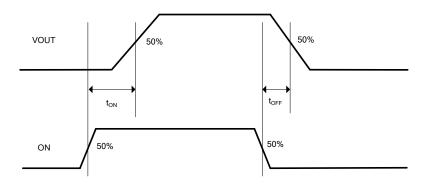


Timing Characteristics (Note 7)

Symbol	Parameters	Test Conditions	Min	Тур	Max	Unit
t _{ON}	Output Turn-on Time		_	720	_	μs
t_{OFF}	Output Turn-off Time	V 5V D 400 0 04v5	_	5	_	μs
t _R	Output Rise Time	$V_{IN} = 5V$, $R_L = 10\Omega$, $C_{OUT} = 0.1\mu F$	_	660	_	μs
t _F	Output Fall Time		_	2.5	_	μs
ton	Output Turn-on Time		_	1050	_	μs
t_{OFF}	Output Turn-off Time	$V_{IN} = 3.3V$, $R_L = 10\Omega$, $C_{OUT} = 0.1\mu F$	_	6.5	_	μs
t _R	Output Rise Time		_	770	_	μs
t_{F}	Output Fall Time		_	3.0	_	μs
ton	Output Turn-on Time		_	2300	_	μs
toff	Output Turn-off Time		_	18	_	μs
t _R	Output Rise Time	$V_{IN} = 1.5V$, $R_L = 10\Omega$, $C_{OUT} = 0.1\mu F$	_	1400	_	μs
t_F	Output Fall Time		_	5.0	_	μs



Output Rise (t_R) and Fall (t_F) Time

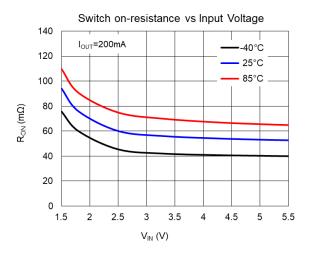


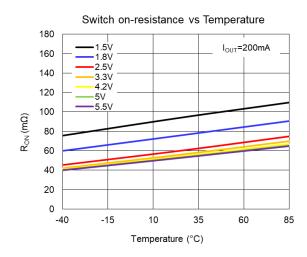
Output Turn On (t_{ON}) and Turn Off (t_{OFF}) Time

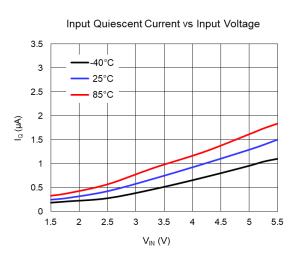
Note: 7. Rise and fall time of the control signal are less than 100ns.

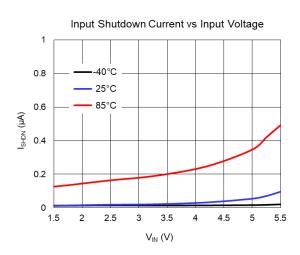


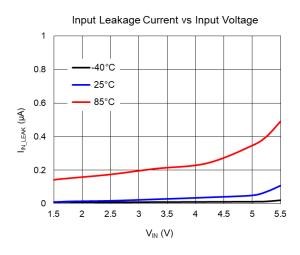
Typical Performance Characteristics ($C_{IN} = 1 \mu F$, $C_{OUT} = 0.1 \mu F$, unless otherwise specified.)

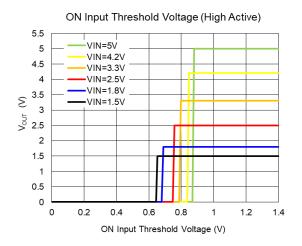






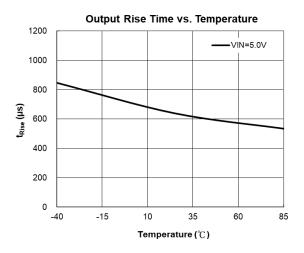


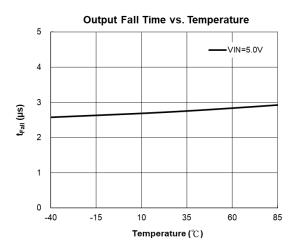


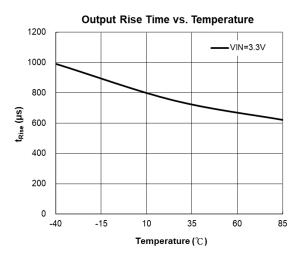


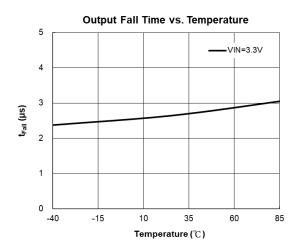


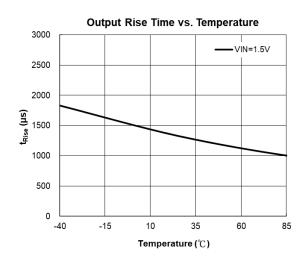
Typical Performance Characteristics (continued) (C_{IN} = 1 μ F, C_{OUT} = 0.1 μ F, R_L = 10 Ω , unless otherwise specified.)

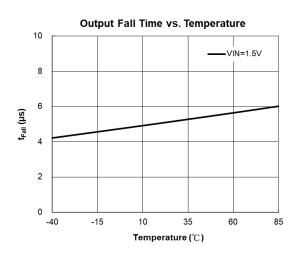






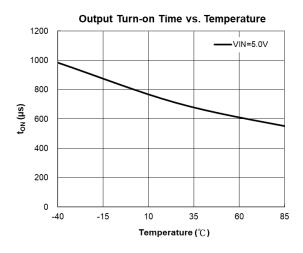


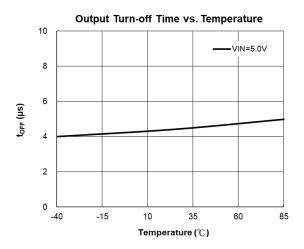


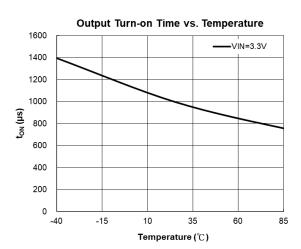


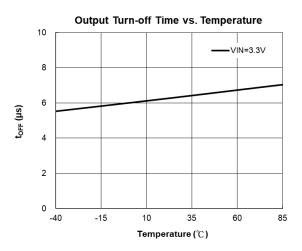


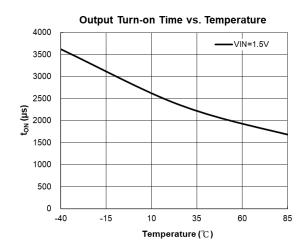
Typical Performance Characteristics (continued) (C_{IN} = 1 μ F, C_{OUT} = 0.1 μ F, R_L = 10 Ω , unless otherwise specified.)

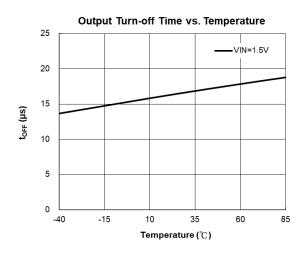






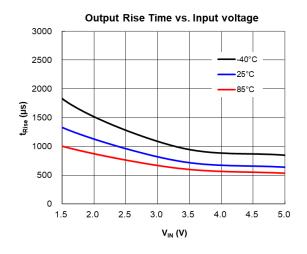


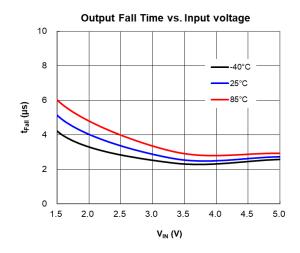


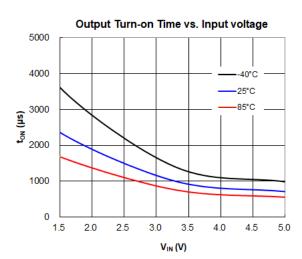


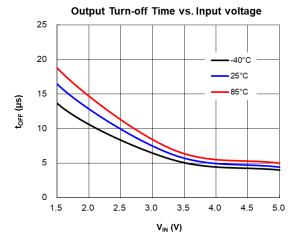


Typical Performance Characteristics (continued) (C_{IN} = 1 μ F, C_{OUT} = 0.1 μ F, R_L = 10 Ω , unless otherwise specified.)



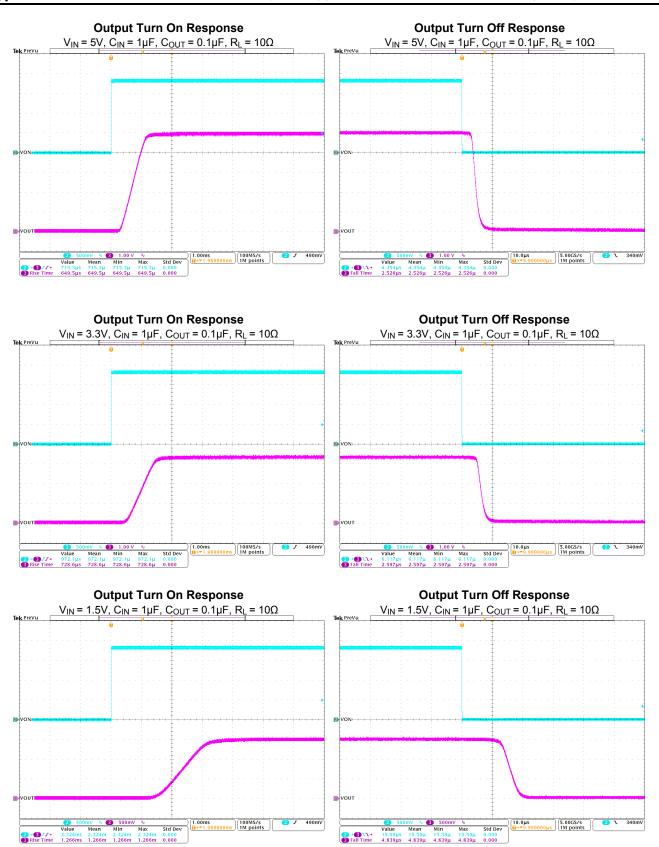






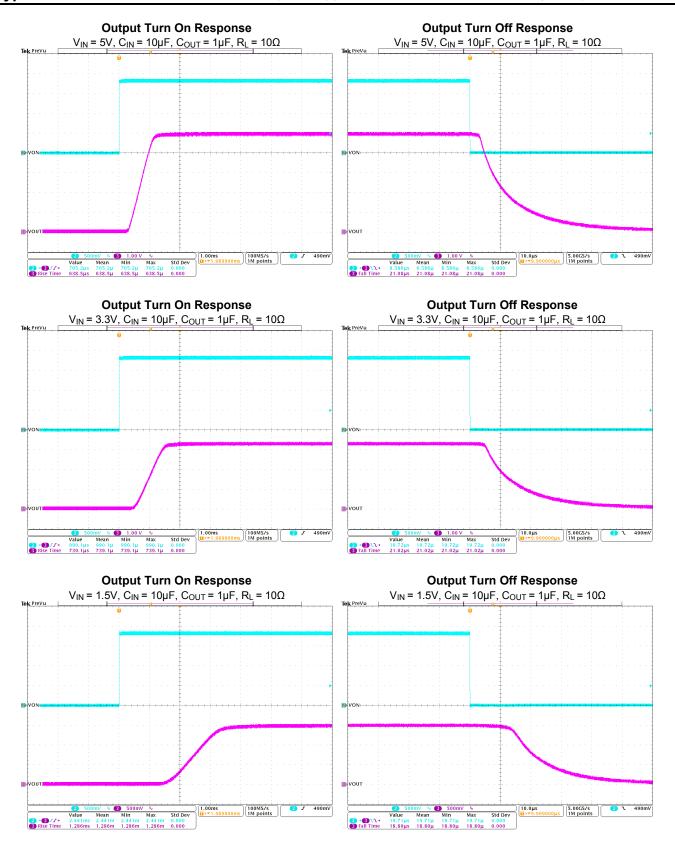


Typical Performance Characteristics (continued) (T_A = +25°C, V_{ON} = 1.8V, unless otherwise specified.)



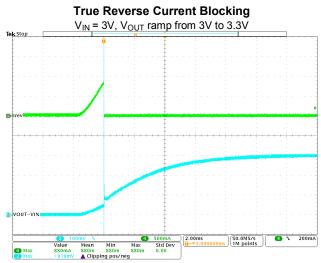


Typical Performance Characteristics (continued) (T_A = +25°C, V_{ON} = 1.8V, unless otherwise specified.)





Typical Performance Characteristics (continued) (T_A = +25°C, C_{IN} = 1 μ F, C_{OUT} = 0.1 μ F, unless otherwise specified.)



May 2021



Application Information

Input Capacitor

A 1µF capacitor is recommended to connect between the V_{IN} and GND pins to decouple glitch and noise of the input power supply. The input capacitor has no specific type or ESR (Equivalent Series Resistance) requirement. However, for higher current application, ceramic capacitors are recommended due to their capability to withstand input current surges from low impedance sources, such as batteries in portable applications. This input capacitor must be located as close as possible to the device to assure input stability and less noise. For PCB layout, a wide copper trace is required for both V_{IN} and GND.

Output Capacitor

The 0.1µF to 1µF capacitor is recommended to connect between the V_{OUT} and GND pins to stabilize and accommodate load transient condition. The output capacitor has no specific type or ESR requirement. The amount of the capacitance may be increased without limit. For PCB layout, the output capacitor must be placed as close as possible to VouT and GND pins. The traces must be kept as short as possible.

Enable/Shutdown Operation

The AP22913 is turned on by setting the ON pin high, and is turned off by pulling it low. To ensure proper operation, the signal source used to drive the ON pin must be able to swing above and below the specified turn-on/off voltage thresholds listed in the Electrical Characteristics section under VIL and VIH.

True Reverse Current Blocking

An internal reverse voltage comparator disables the power-switch when the output voltage (V_{OUT}) is driven higher than the input voltage (V_{IN}), by V_{T RCB}, to quickly (10µs typ) stop the flow of current towards the input side of the switch.

Reverse current protection is always active, even when the power switch is disabled. Additionally, undervoltage lockout (UVLO) protection turns the switch off if the input voltage is too low.

Discharge Operation

The AP22913 offers a discharge option that helps to discharge the output charge when disabled.

Power Dissipation

The maximum IC junction temperature should be restricted to +125°C under normal operating conditions. The device power dissipation and proper sizing of the thermal plane is critical to avoid thermal shutdown and ensure reliable operation. Power dissipation of the device depends on input voltage and load conditions and can be calculated by:

$$P_{D} = I_{OUT}^{2} x R_{DSON}$$
 (1)

However, the maximum power dissipation that can be handled by the device depends on the maximum junction to ambient thermal resistance, maximum ambient temperature, and maximum device junction temperature, which can be approximated by the equation below:

$$P_{D(MAX)} = \frac{(125^{\circ}C - T_A)}{\theta_{JA}}$$
 (2)

Layout Guidelines

Good PCB layout is important for improving the thermal performance of the device. All trace lengths should be kept as short as possible. The input (V_{IN}) and output (V_{OUT}) PCB traces should be as wide as possible to reduce stray impedance.

Use a ground plane to enhance the power dissipation capability of the device if applicable. Place input and output capacitors close to the device to minimize the effects of parasitic inductance.

13 of 17 AP22913 © Diodes Incorporated Document number: DS41203 Rev. 6 - 2 www.diodes.com



Ordering Information



W6: SOT-26

Part Number	Package Code	Booksging	7" Tape and Reel	
Part Number	Package Code	Packaging	Quantity	Part Number Suffix
AP22913CN4-7	CN4	X1-WLB0909-4	3,000/Tape & Reel	-7
AP22913W6-7	W6	SOT26	3,000/Tape & Reel	-7

Marking Information

(1) X1-WLB0909-4

(Top View)

X ΥW X: Identification Code

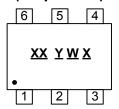
Y: Year: 0~9

W: Week: A~Z: 1~26 week; a~z: 27~52 week; z represents 52 and 53 week

Part Number	Package	Identification Code
AP22913CN4-7	X1-WLB0909-4	C

(2) SOT-26





XX: Identification Code

Y : Year 0~9

W : Week : A~Z : 1~26 week; a~z : 27~52 week; z represents

52 and 53 week

X: Internal Code

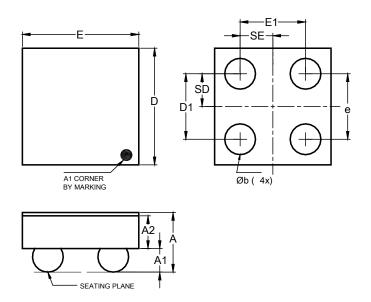
Part Number	Package	Identification Code
AP22913W6-7	SOT26	N9



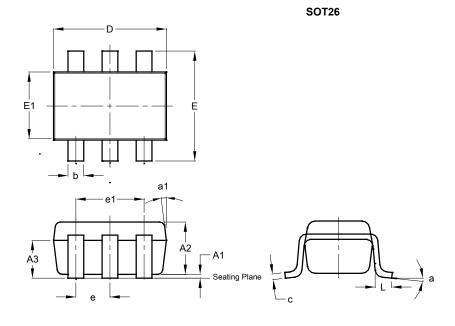
Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

X1-WLB0909-4



X1-WLB0909-4					
Dim	Min Max		Тур		
Α	0.410	0.500	0.455		
A1	0.160	0.200	0.180		
A2	0.225	0.275	0.250		
b	0.215	0.255	0.235		
D	0.840	0.900	0.870		
D1	0.450	0.550	0.500		
Е	0.840	0.900	0.870		
E1	0.450	0.550	0.500		
е	0.500 BSC				
SD	0.250 BSC				
SE	0.250 BSC				
All	Dimens	ions in	mm		



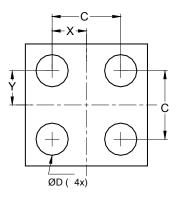
SOT26						
Dim	Min	Max	Тур			
A1	0.013	0.10	0.05			
A2	1.00	1.30	1.10			
A3	0.70	0.80	0.75			
b	0.35	0.50	0.38			
С	0.10	0.20	0.15			
D	2.90	3.10	3.00			
е	-	-	0.95			
e1	-	-	1.90			
Е	2.70	3.00	2.80			
E1	1.50	1.70	1.60			
L	0.35	0.55	0.40			
а	-	-	8°			
a1	-	-	7°			
All Dimensions in mm						



Suggested Pad Layout

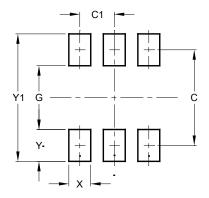
Please see http://www.diodes.com/package-outlines.html for the latest version.

X1-WLB0909-4



Dimensions	Value
	(in mm)
C	0.500
D	0.235
Х	0.250
Y	0.250

SOT26



Dimensions	Value (in mm)
С	2.40
C1	0.95
G	1.60
Х	0.55
Y	0.80
Y1	3.20



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